

Replaces DS5967-4

DS5967-5

July 2024

(LN43475)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Medium Voltage Soft Starts
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

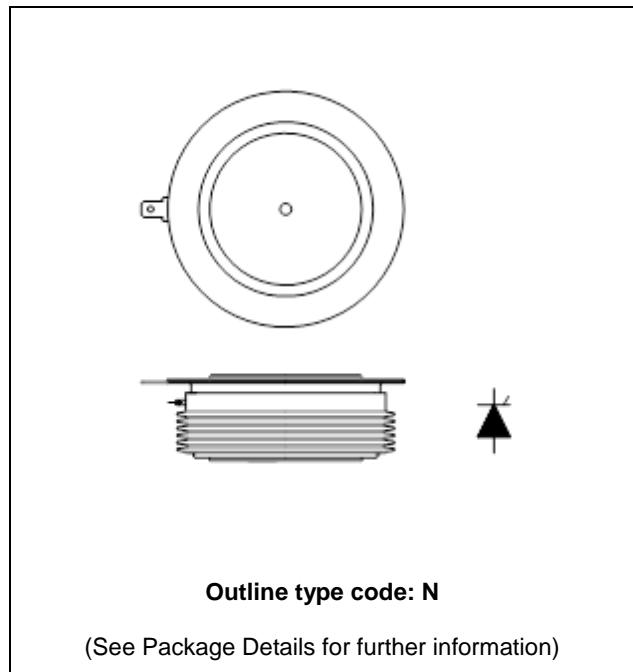
Part and Ordering Number	Repetitive Peak Voltages V_{DRM} and V_{RRM} (V)	Conditions
DCR1150N42	4200	$T_{vj} = -40^{\circ}\text{C}$ to 125°C , $I_{DRM} = I_{RRM} = 100\text{mA}$, V_{DRM}, V_{RRM} $t_p = 10\text{ms}$
DCR1150N40	4000	$V_{DSM} & V_{RSM} =$ $V_{DRM} & V_{RRM} + 100\text{V}$ respectively

Lower voltage grades available.

KEY PARAMETERS

V_{DRM}	4200V
$I_{T(AV)}$	1160A
I_{TSM}	16800A
dV/dt^*	1500V/μs
dl/dt	1000A/μs

* Higher dV/dt selections are available on request



ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

Fig. 1 Package outline

For example:

DCR1150N42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

CURRENT RATINGS

$T_{case} = 60^\circ\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	1160	A
$I_{T(RMS)}$	RMS value	-	1820	A
I_T	Continuous (direct) on-state current	-	1680	A

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I_{tsm}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^\circ\text{C}$ $V_R = 0$	16.8	kA
I^2t	I^2t for fusing		1.41	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	DC	-	22.0	°C/kW
		Single side cooled	Anode DC	-	40.5	°C/kW
			Cathode DC	-	50.1	°C/kW
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 23kN (with mounting compound)		Double side	-	4.0 °C/kW
				Single side	-	8.0 °C/kW
T_{vj}	Virtual junction temperature	Blocking V_{DRM} / V_{RRM}		-	125	°C
T_{stg}	Storage temperature range			-55	125	°C
F_m	Clamping force			20	25	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Max.	Units
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^\circ C$	-	100	mA
V_{TM}	Instantaneous forward voltage	At 2900A peak, $T_j = 25^\circ C$	1.81	1.95	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^\circ C$, gate open	-	1500	V/ μ s
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{T(AV)}$	Repetitive 50Hz	-	A/ μ s
		Gate source 30V, 10Ω $t_r < 0.5\mu s$, $T_j = 125^\circ C$	Non-repetitive	-	1000
$V_{T(TO)}$	Threshold voltage - Low level	300A to 900A at $T_{case} = 125^\circ C$	-	0.86	V
	Threshold voltage - High level	900A to 4000A at $T_{case} = 125^\circ C$	-	1.01	V
r_T	On-state slope resistance - Low level	300A to 900A at $T_{case} = 125^\circ C$	-	0.60	mΩ
	On-state slope resistance - High level	900A to 4000A at $T_{case} = 125^\circ C$	-	0.44	mΩ
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω $t_r = 0.5\mu s$, $T_j = 25^\circ C$	-	3	μ s
t_q	Turn-off time	$T_j = 125^\circ C$, $I_{peak} = 1000A$, $t_p = 1000\mu s$, $V_{RM} = 100V$, $dl/dt = 5A/\mu s$, $dV_{DR}/dt = 20V/\mu s$ linear to 2500V	-	800	μ s
Q_s	Stored charge	$I_T = 1000A$, $t_p = 1000\mu s$, $T_j = 125^\circ C$, $dl/dt = 5A/\mu s$, V_R peak = 100V. [LEM]	2000	3500	μ C
I_{RR}	Reverse recovery current		80	120	A
Q_s	Stored charge	$T_j = 125^\circ C$, $dl/dt = 1A/\mu s$,	(Typ.) 2270		μ C
I_{RR}	Reverse recovery current		(Typ.) 40		A
I_L	Latching current	$T_j = 25^\circ C$, $V_D = 5V$	-	3	A
I_H	Holding current	$T_j = 25^\circ C$, $R_{G-K} = \infty$, $I_{TM} = 500A$, $I_T = 5A$	-	300	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^\circ C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V_{DRM} , $T_{case} = 125^\circ C$	0.4	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^\circ C$	350	mA
I_{GD}	Gate non-trigger current	At 50% V_{DRM} , $T_{case} = 125^\circ C$	15	mA

CURVES

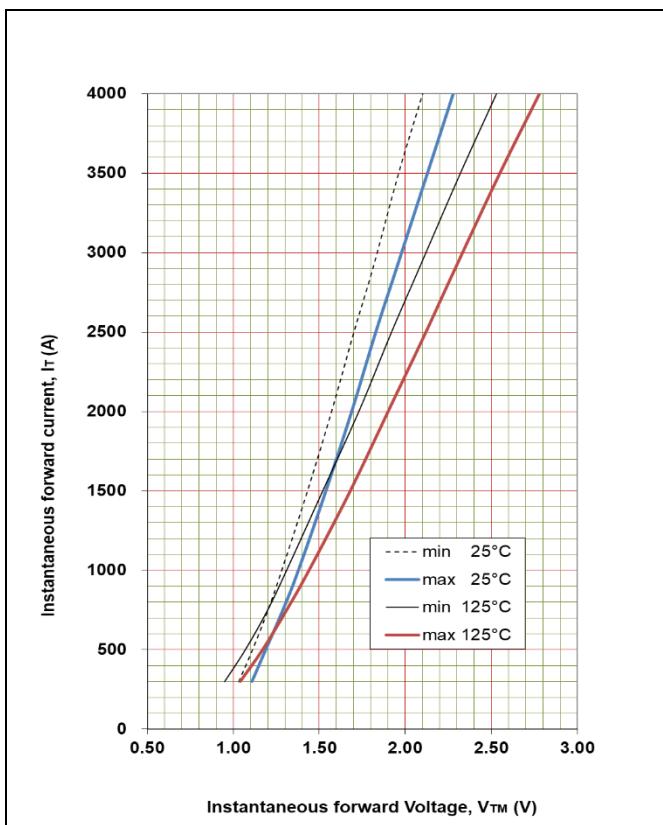


Fig. 2 Maximum & minimum on state characteristics

V_{TM} EQUATION

$$V_{TM} = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where $A = 0.277850$

$B = 0.119589$

$C = 0.000413$

$D = -0.002540$

These values are valid for $T_j = 125^\circ C$ for I_T 300A to 4000A

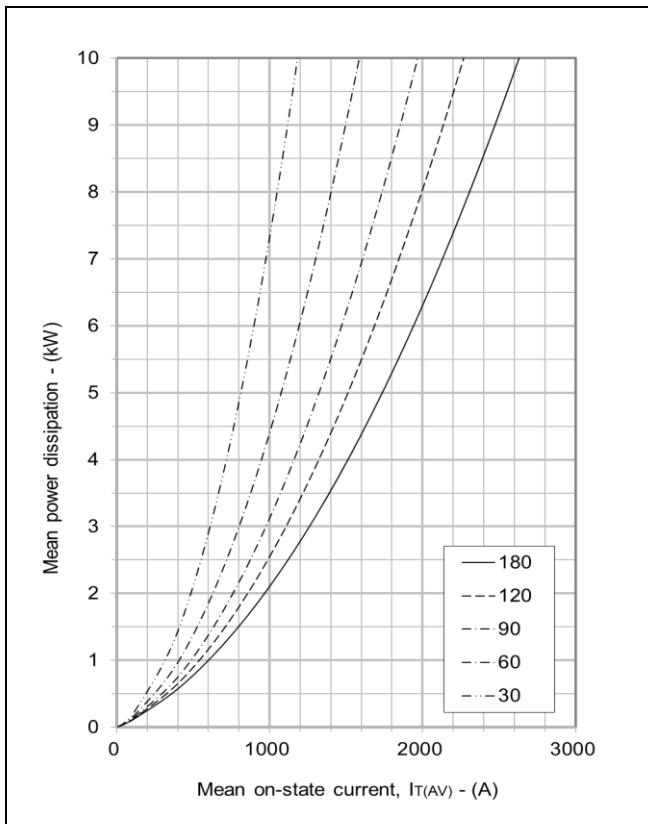


Fig. 3 On-state power dissipation - sine wave

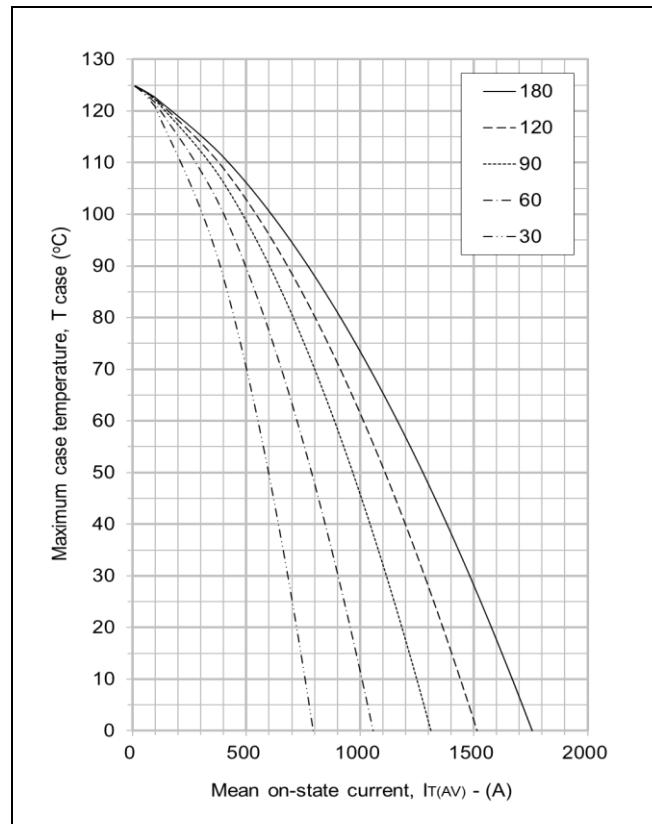


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

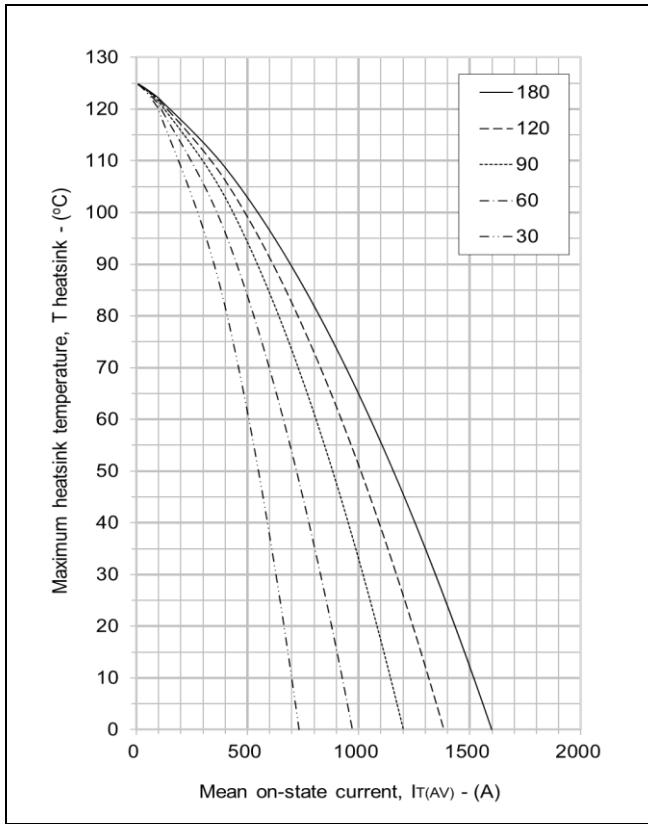


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

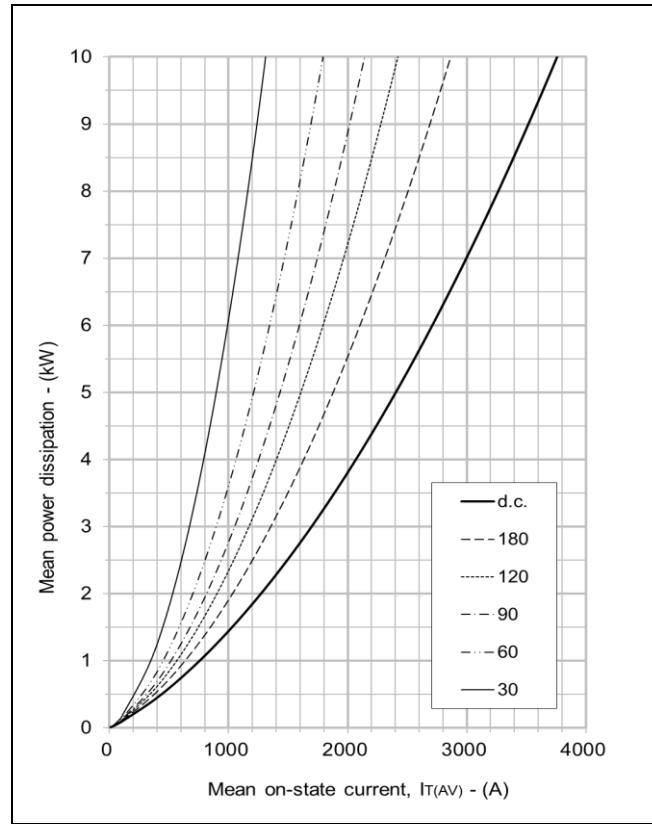


Fig. 6 On-state power dissipation - rectangular wave

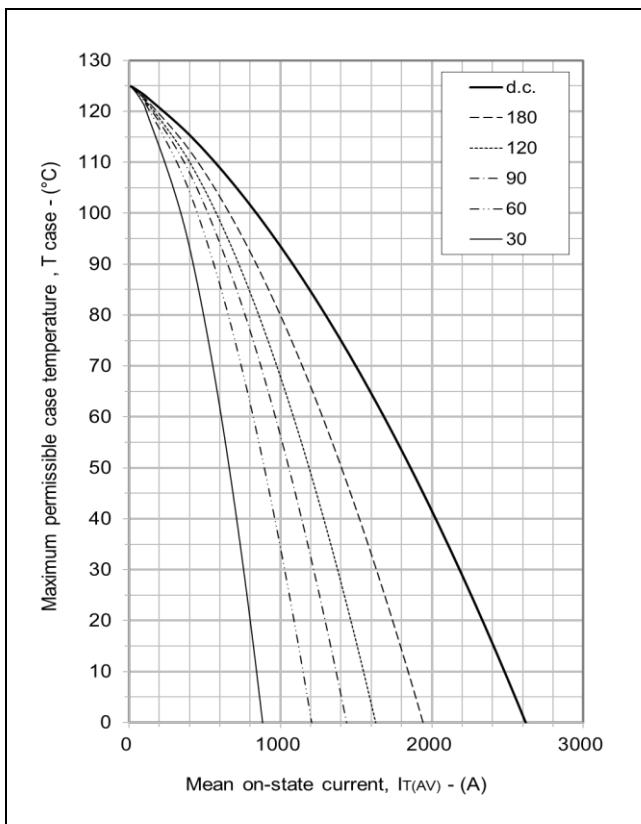


Fig. 7 Maximum permissible case temperature,
double side cooled - rectangular wave

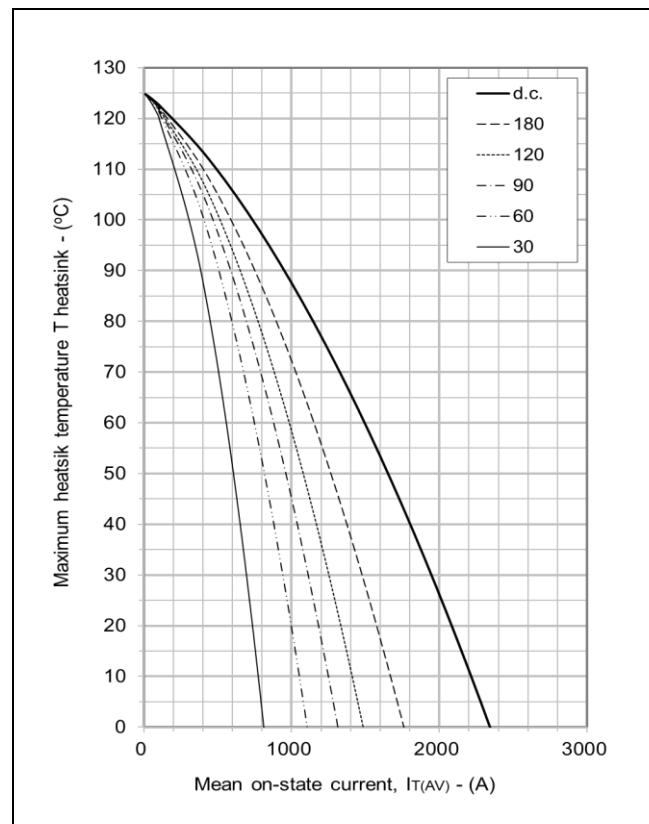


Fig. 8 Maximum permissible heatsink temperature,
double side cooled - rectangular wave

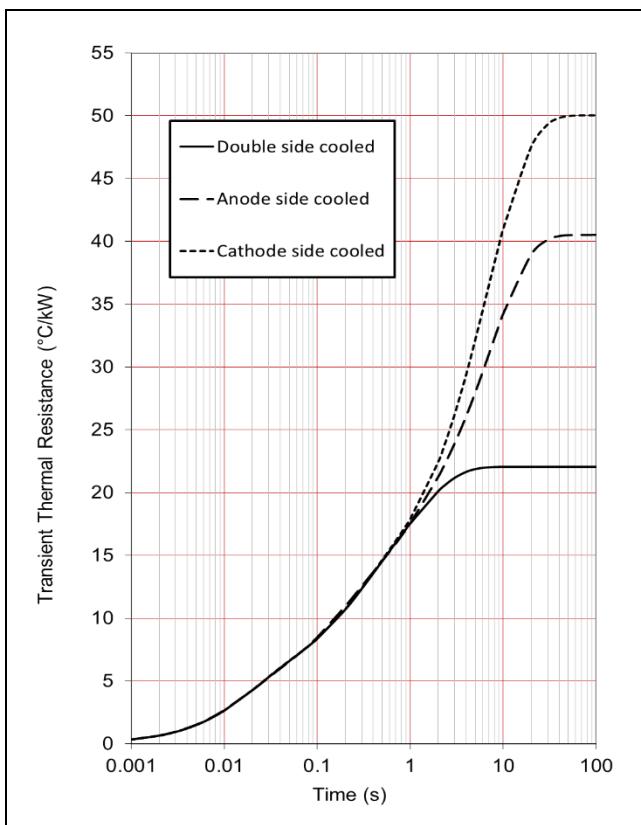


Fig. 9 Maximum (limit) transient thermal impedance – junction to case (degC/kW)

		1	2	3	4
Double side cooled	Ri(°C/kW)	3.473	4.905	9.146	4.522
	Ti(s)	0.146	0.017	1.283	0.377
Anode side cooled	Ri(°C/kW)	6.039	4.278	5.130	25.087
	Ti(s)	0.136	0.014	0.659	7.236
Cathode side cooled	Ri(°C/kW)	7.667	5.053	9.736	27.599
	Ti(s)	0.224	0.017	4.057	8.278

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

ΔR_{θ(j-c)} Conduction

Tables show the increments of thermal resistance R_{θ(j-c)} when the device operates at conduction angles other than d.c.

Double side cooling		Anode Side Cooling		Cathode Sided Cooling	
θ°	ΔZ _{th} (z)	θ°	ΔZ _{th} (z)	θ°	ΔZ _{th} (z)
180	3.03	2.07	180	3.03	2.12
120	3.49	2.95	120	3.49	3.04
90	3.99	3.43	90	3.99	3.54
60	4.43	3.94	60	4.43	4.08
30	4.77	4.49	30	4.76	4.66
15	4.92	4.77	15	4.92	4.97

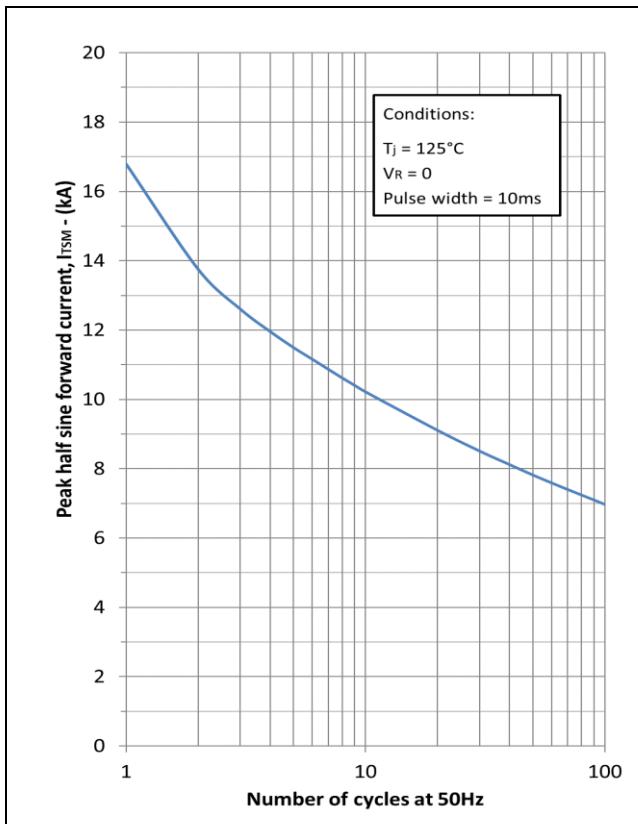


Fig. 10 Multi-cycle surge current

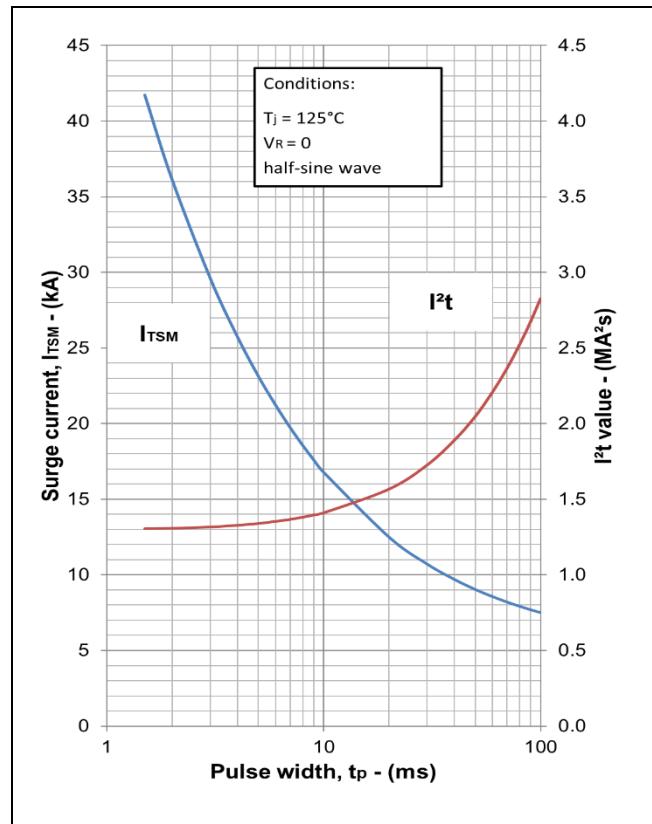


Fig. 11 Single-cycle surge current

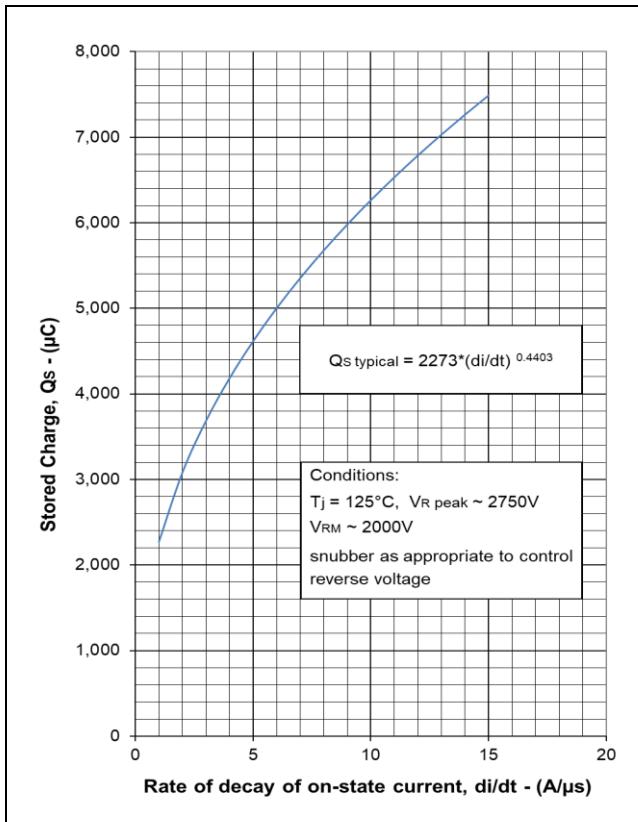


Fig. 12 Stored charge

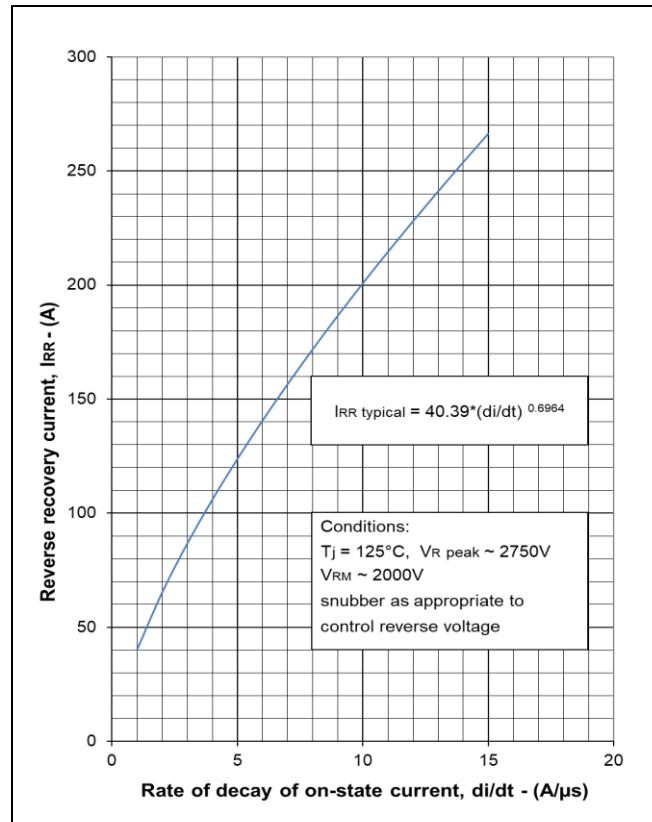


Fig. 13 Reverse recovery current

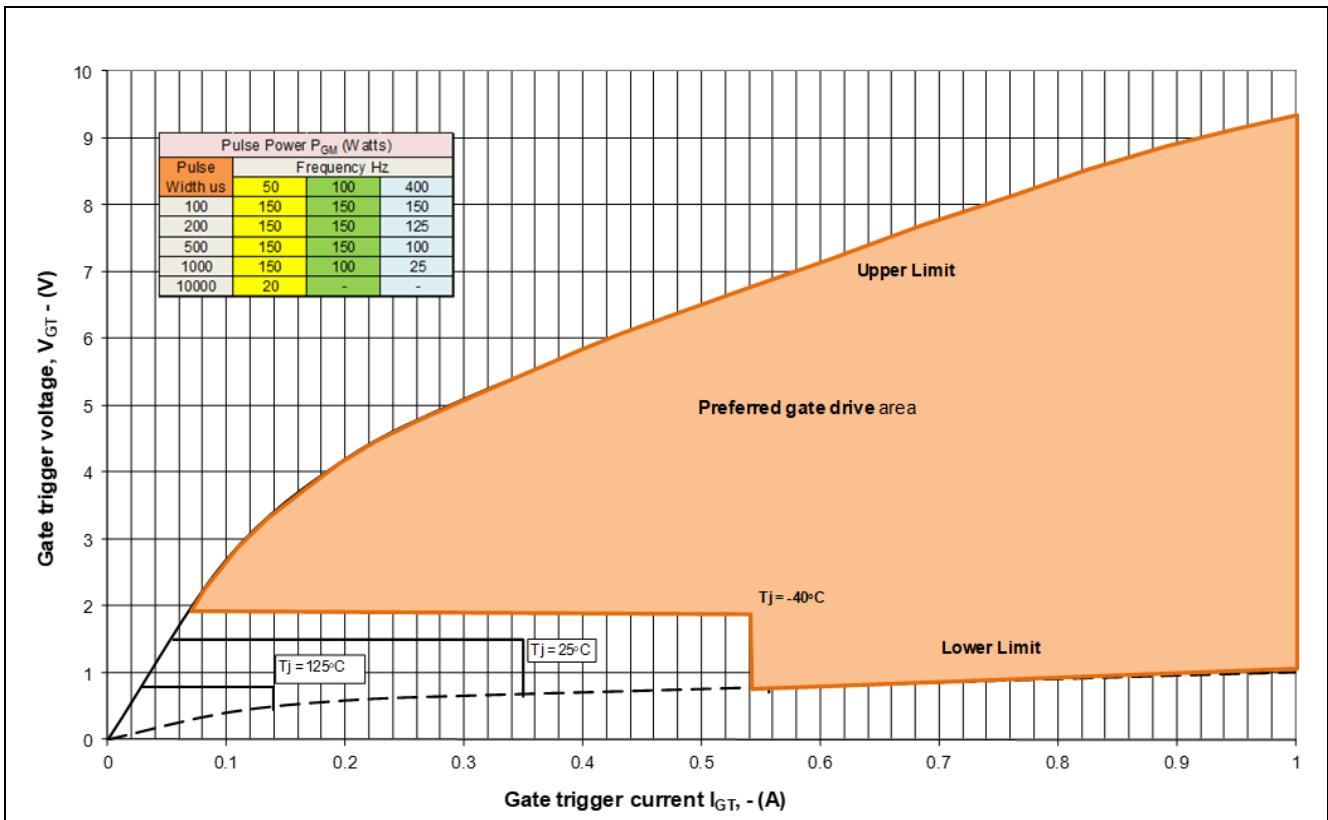


Fig. 14 Gate characteristics

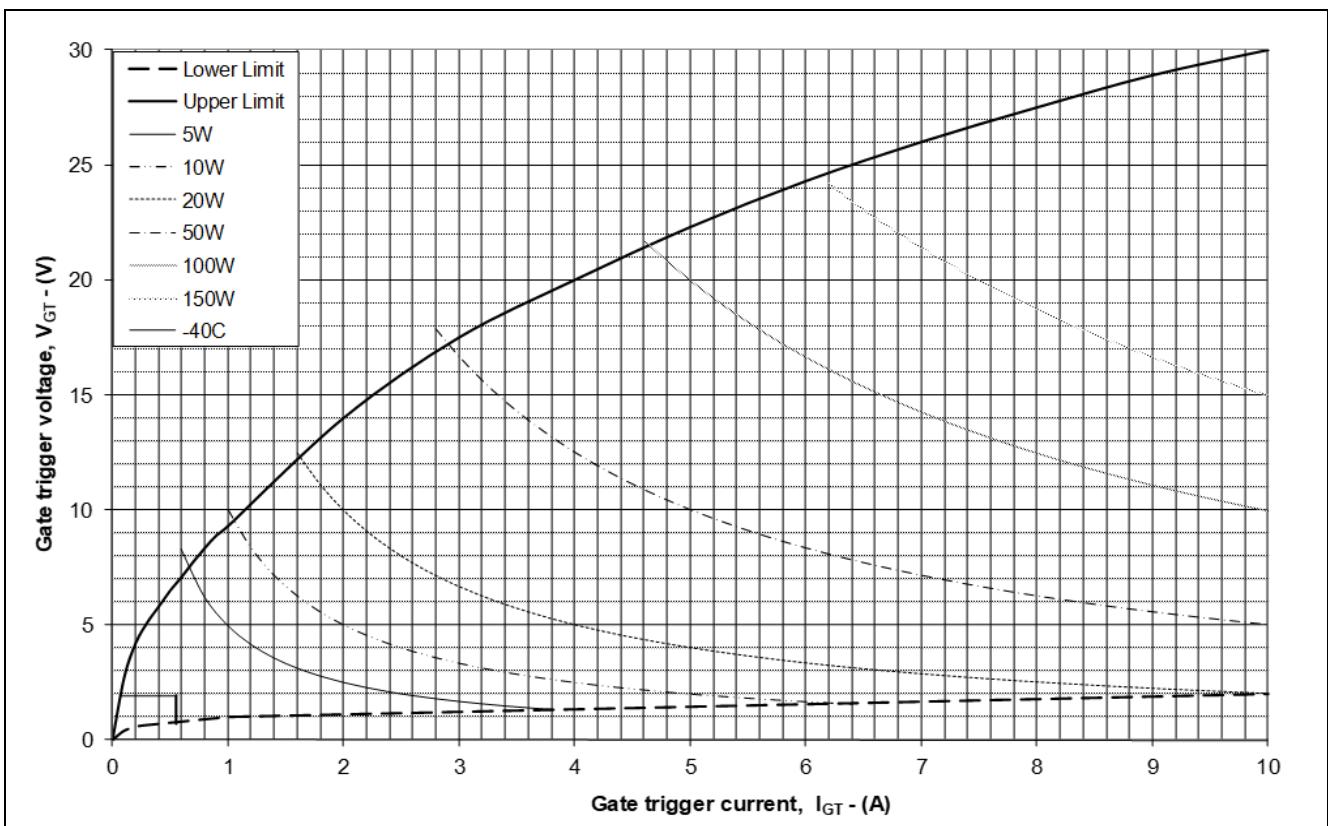


Fig. 15 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

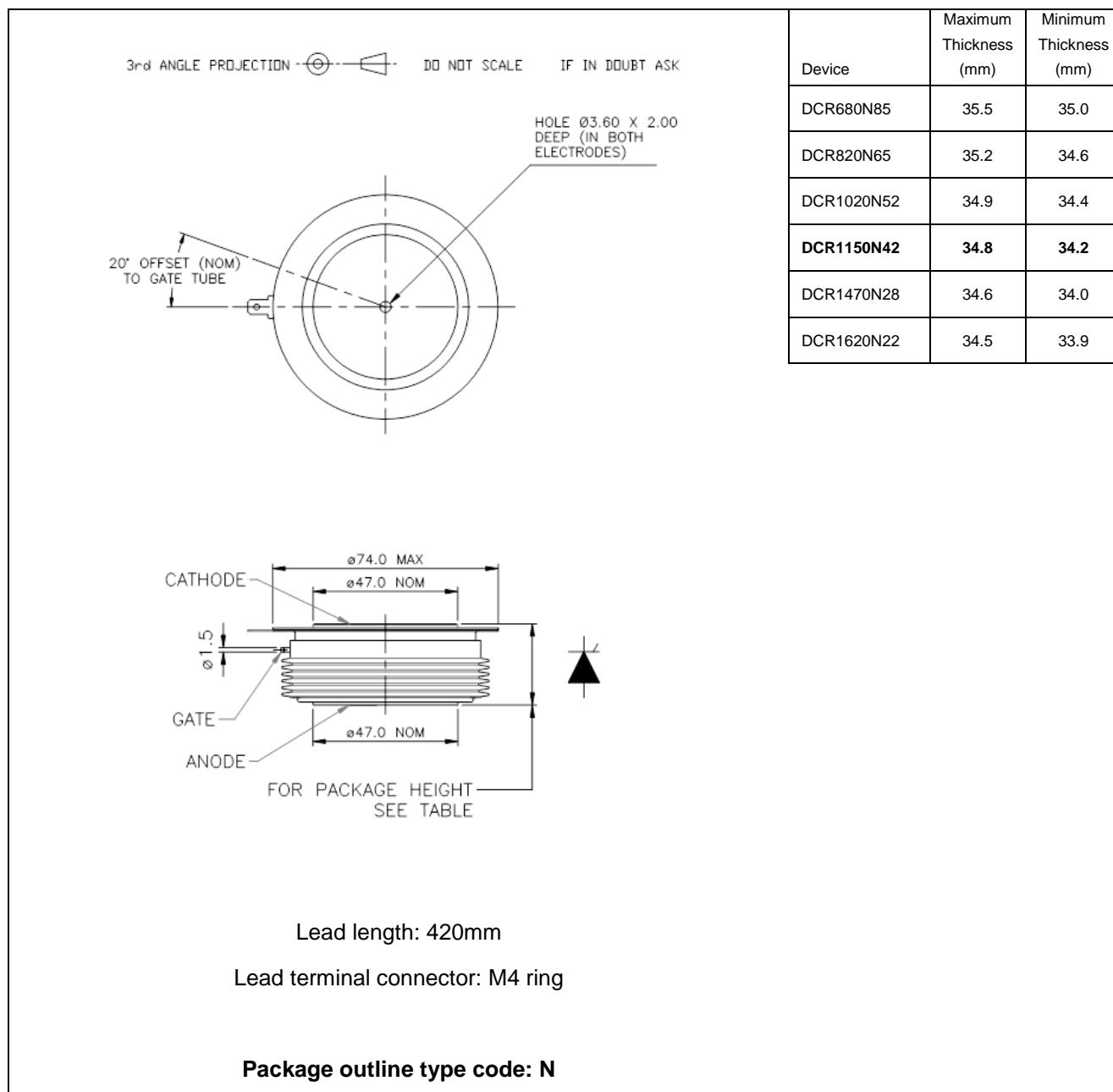


Fig. 16 Package outline

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HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LIMITED
Doddington Road, Lincoln, Lincolnshire. LN6 3LF
United Kingdom.
Phone: +44 (0) 1522 500500

Web: <http://www.dynexsemi.com>

CUSTOMER SERVICE

Phone: +44 (0) 1522 502753 / 502901
e-mail: powersolutions@dynexsemi.com